

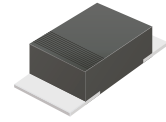
CURMT103-HF Thru. CURMT107-HF

Reverse Voltage: 200 to 1000 Volts

Forward Current: 1.0 Amp

RoHS Device

Halogen Free

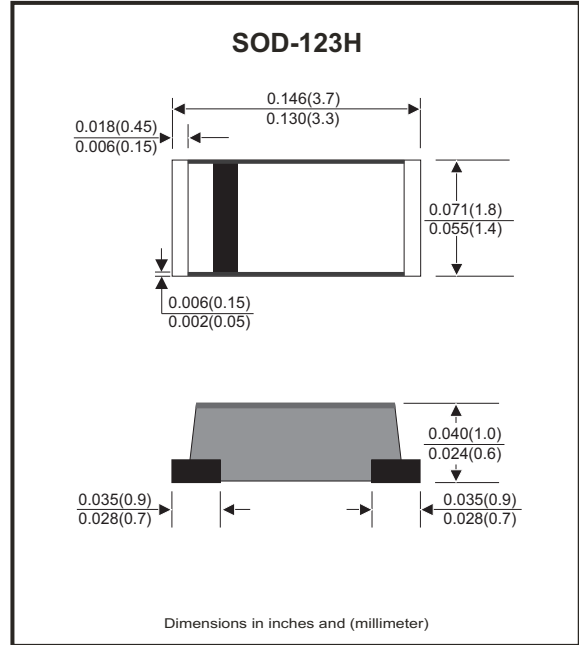


Features

- Excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Tiny plastic SMD package.
- High current capability.
- Ultrafast recovery time for high efficiency.
- High surge current capability.
- Glass passivated chip junction.
- Lead-free part meets RoHS requirements.

Mechanical data

- Epoxy: UL94V-0 rated flame retardant.
- Case: Molded plastic, SOD-123H/MINI SMA
- Terminals: Solderable per MIL-STD-750, Method 2026.
- Polarity: Indicated by cathode band.
- Mounting Position: any
- Weight: 0.011 grams approx.



Circuit diagram



Maximum Ratings and Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Symbol	CURMT 103-HF	CURMT 104-HF	CURMT 107-HF	Unit
Max. Repetitive peak reverse voltage	V _{RRM}	200	400	1000	V
Max. Continuous reverse voltage	V _R	200	400	1000	V
Max. RMS voltage	V _{RMS}	140	280	700	V
Max. Forward rectified current	I _O	1.0			A
Max. Forward voltage @ I _F =1.0A	V _F	1.00	1.30	1.70	V
Max. Reverse recovery time (note 1)	T _{RR}	50		75	ns
Max. Forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	25			A
Max. Reverse current	V _R =V _{RRM} T _J =25°C	5.0			μA
	V _R =V _{RRM} T _J =125°C	150			
Typ. Thermal resistance Junction to ambient air	R _{θJA}	42			°C/W
Typ. Diode Junction capacitance f=1MHz and applied 4V DC reverse voltage	C _J	20			pF
Operating junction temperature	T _J	-55 to +150			°C
Storage temperature range	T _{STG}	-65 to +175			°C

Note 1. Reverse recovery time test condition, I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

2. Company reserves the right to improve product design, functions and reliability without notice.

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REV: C

Rating and Characteristic Curves (CURMT103-HF Thru. CURMT107-HF)

Fig.1 - Typical Forward Characteristics

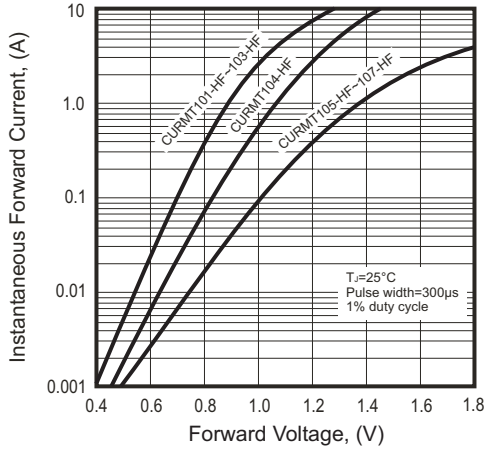


Fig.2 - Typical Forward Current Derating Curve

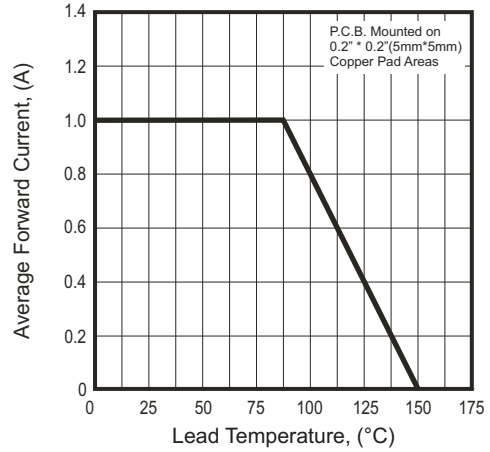
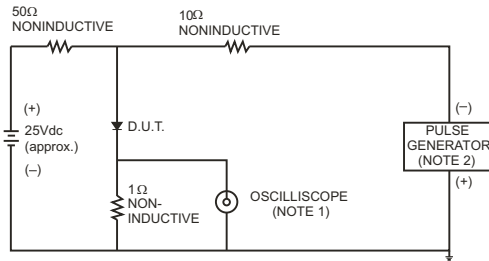


Fig.3- Test circuit diagram and reverse recovery time characteristics



NOTES: 1. Rise Time = 7ns max., Input Impedance = 1 megohm, 22pF.
2. Rise Time = 10ns max., Source Impedance = 50 ohms.

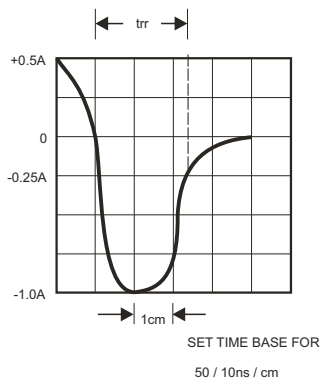


Fig.4- Maximum non-repetitive forward surge current

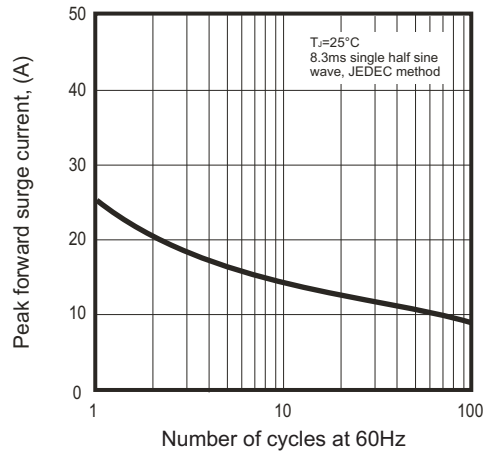
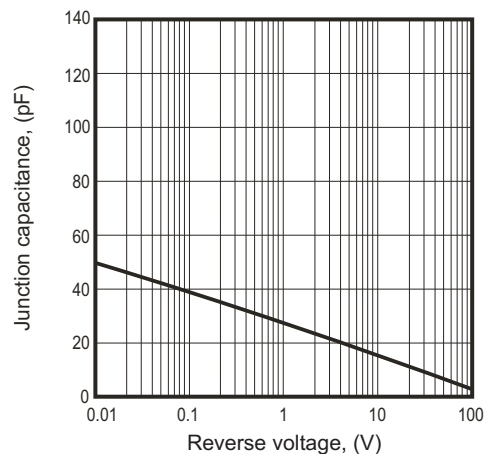
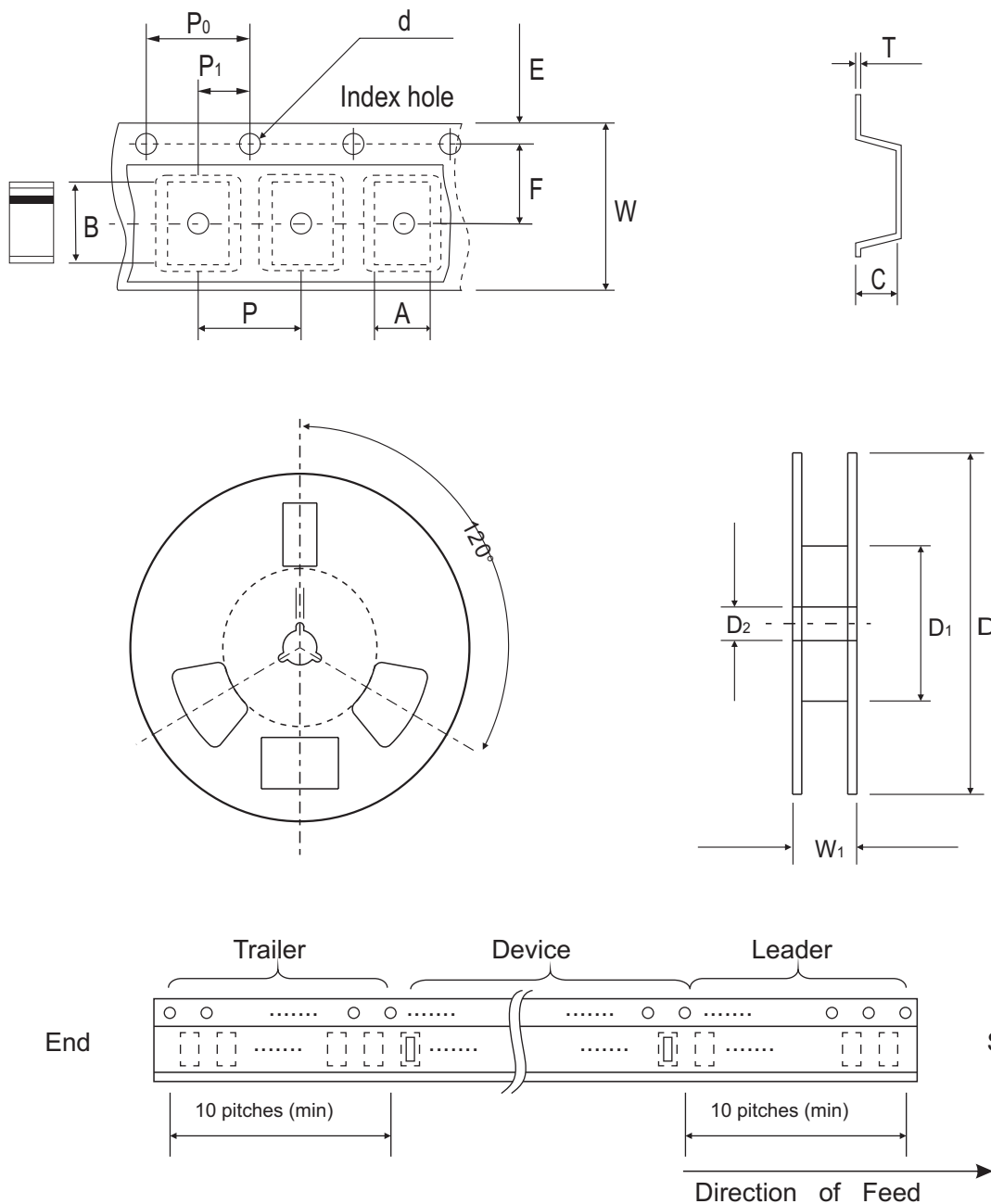


Fig.5- Typical Junction Capacitance



Reel Taping Specification



SOD-123H	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	2.00 ± 0.10	3.85 ± 0.10	1.10 ± 0.10	1.50 ± 0.10	178.00 ± 2.00	62.00 (min)	13.00 ± 0.50
	(inch)	0.079 ± 0.004	0.152 ± 0.004	0.043 ± 0.004	0.059 ± 0.004	7.007 ± 0.079	2.441 (min)	0.512 ± 0.020

SOD-123H	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	3.50 ± 0.10	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.23 ± 0.10	8.00 ± 0.30	11.40 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.004	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.009 ± 0.04	0.315 ± 0.012	0.449 ± 0.039